TOSHIBA 2SC5332

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2 S C 5 3 3 2

HORIZONTAL DEFLECTION OUTPUT FOR HIGH RESOLUTION DISPLAY, COLOR TV

HIGH SPEED SWITCHING APPLICATIONS

High Voltage $: V_{CBO} = 1700 V$

Low Saturation Voltage: $V_{CE (sat)} = 3 V (Max.)$

High Speed : $t_f = 0.15 \,\mu s$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTER	SYMBOL	RATING	UNIT		
Collector-Base Voltage		v_{CBO}	1700	V	
Collector-Emitter Voltage		v_{CEO}	800	V	
Emitter-Base Voltage		$V_{ m EBO}$	5	V	
Collector Current	DC	$I_{\mathbf{C}}$	14	A	
	Pulse	I_{CP}	28		
Base Current		I_{B}	7	A	
Collector Power Dissipation (Tc = 25°C)		PC	200	w	
Junction Temperature		T_j	150	$^{\circ}\mathrm{C}$	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	

Unit in mm 5.45 ± 0.15 1. BASE 2. COLLECTOR (HEAT SINK) 3. EMITTER **JEDEC EIAJ** TOSHIBA 2-21F2A

Weight: 9.75 g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{CB} = 1700 \text{ V}, I_{E} = 0$	<u> </u>	_	1	mA
Emitter Cut-off Current	I _{EBO}	$V_{EB} = 5 V, I_{C} = 0$	_		100	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C} = 10 {\rm mA}, \; I_{\rm B} = 0$	800	_	_	V
DC Current Gain	h _{FE} (1)	$V_{CE} = 5 V$, $I_{C} = 1 A$	10		30	
DC Current Gain	h _{FE} (2)	$V_{CE} = 5 V, I_{C} = 8 A$	4	_	8.5	1 - 1
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_{C} = 8 \text{ A}, I_{B} = 2 \text{ A}$	_	_	3	V
Base-Emitter Saturation Voltage	V _{BE} (sat)	$I_{C} = 8 \text{ A}, I_{B} = 2 \text{ A}$	_	1.3	1.5	V
Transition Frequency	${ m f_T}$	$V_{CE} = 10 \text{ V}, I_{E} = 0.1 \text{ A}$	_	3	-	MHz
Collector Output Capacitance	Cob	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$		230	l —	pF
Switching Storage Time	t_{stg}	$I_{CP} = 7 \text{ A}, I_{B1} \text{ (end)} = 1.4 \text{ A}$		2.0	3.5	
Time Fall Time	tf	$ m f_{ m H} = 64~kHz$	_	0.15	0.3	μ\$

961001EAA2

TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.

The information contained herein is subject to change without notice.







